

ROPPERI

Uli Einhaus

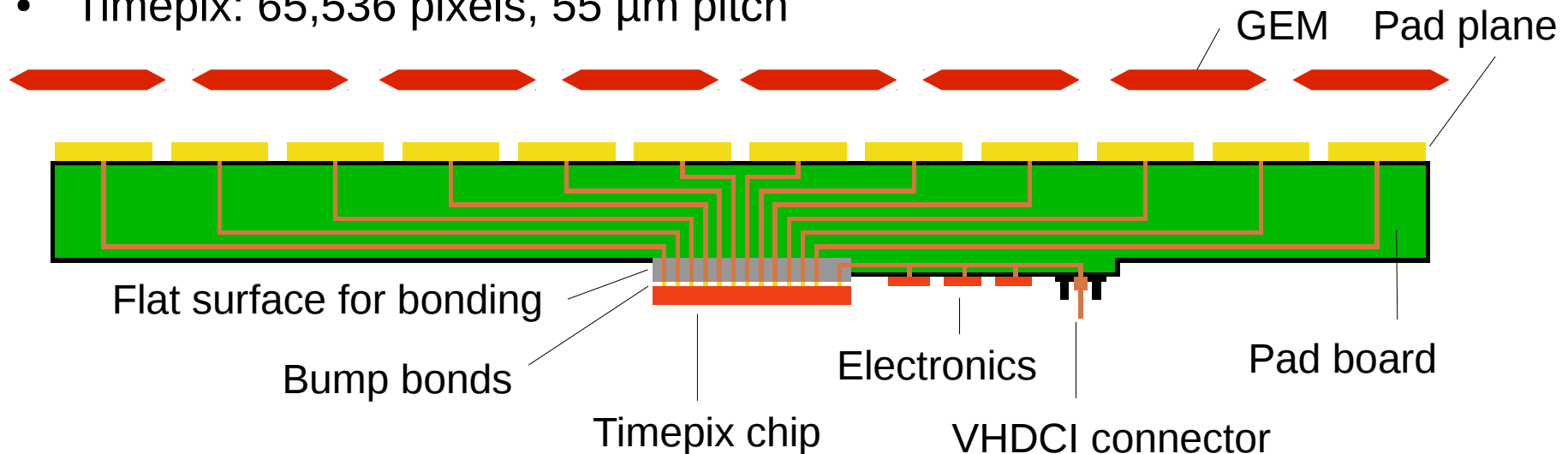
LCTPC Collaboration Meeting

09.01.2019

HELMHOLTZ
RESEARCH FOR GRAND CHALLENGES

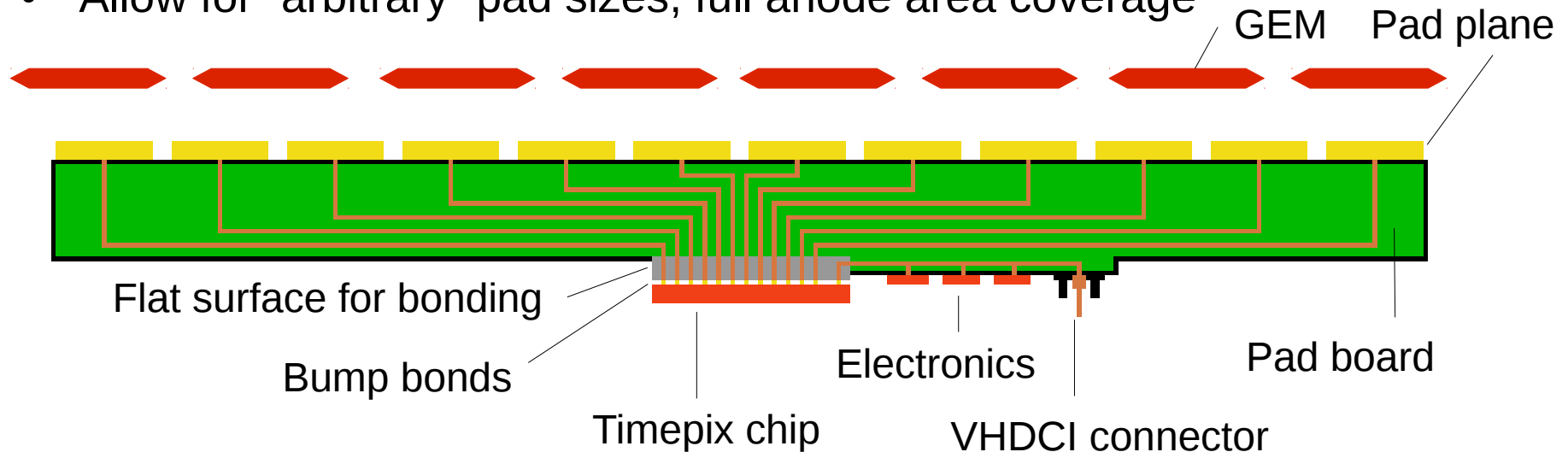


- GEMs, small pads, Timepix chip as readout electronics
- Connections from pads to chip are routed through the board, then bump bonded to the chip
- Timepix wirebond pads for the communication channels are on the same side as the pixels → also bump bonded, back to the board
- Timepix: 65,536 pixels, 55 μm pitch



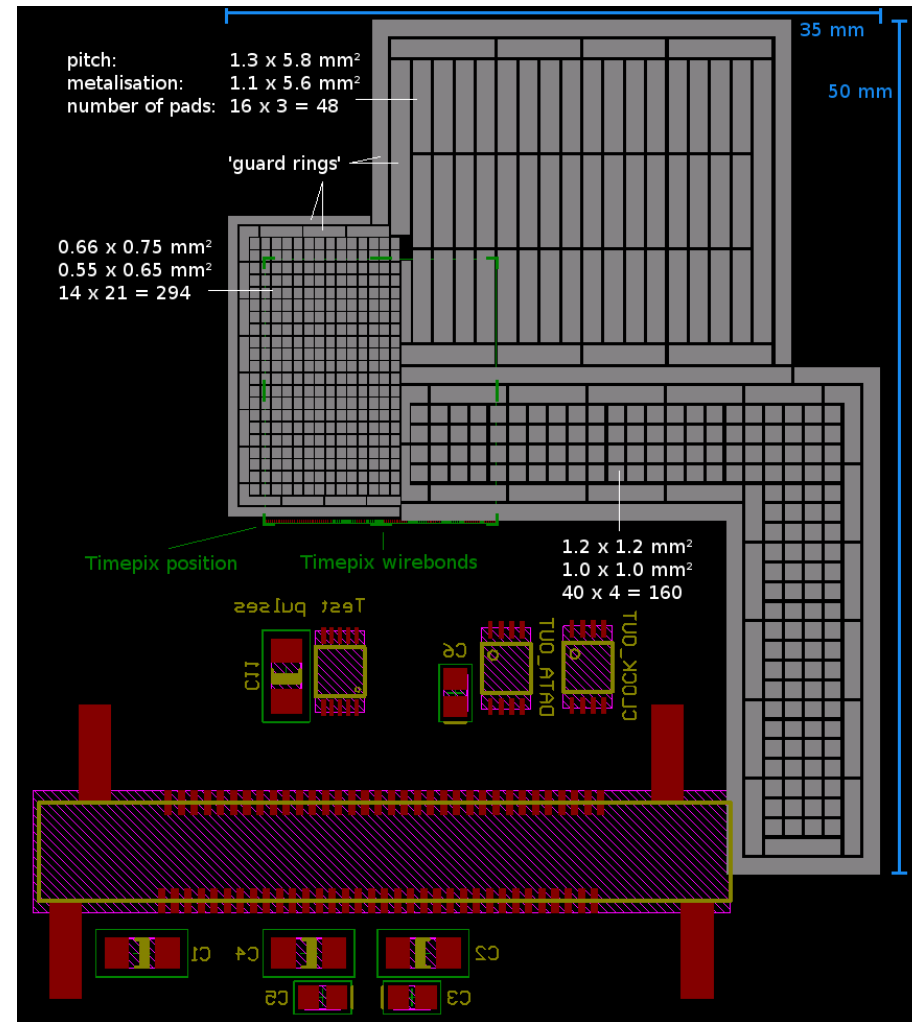
Benefits

- Compared to the existing GEMs+pads system:
 - Higher granularity → better occupancy, double track resolution, possible cluster counting
 - Square pads, several pads per charge cloud → no $\tan^2\theta$ -effect
 - High integration: $O(30)$ smaller footprint
- Allow for “arbitrary” pad sizes, full anode area coverage



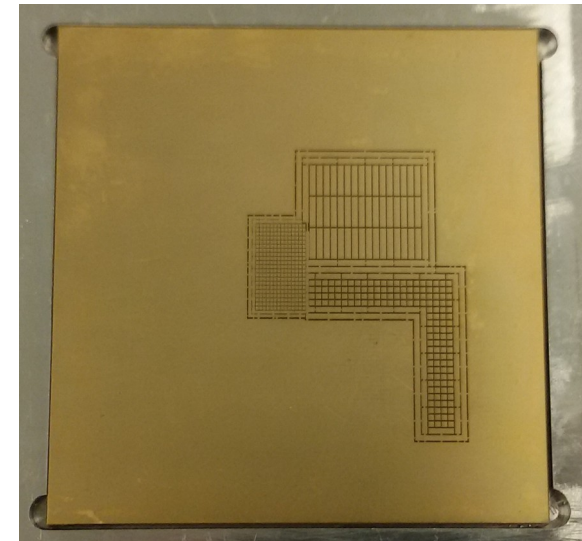
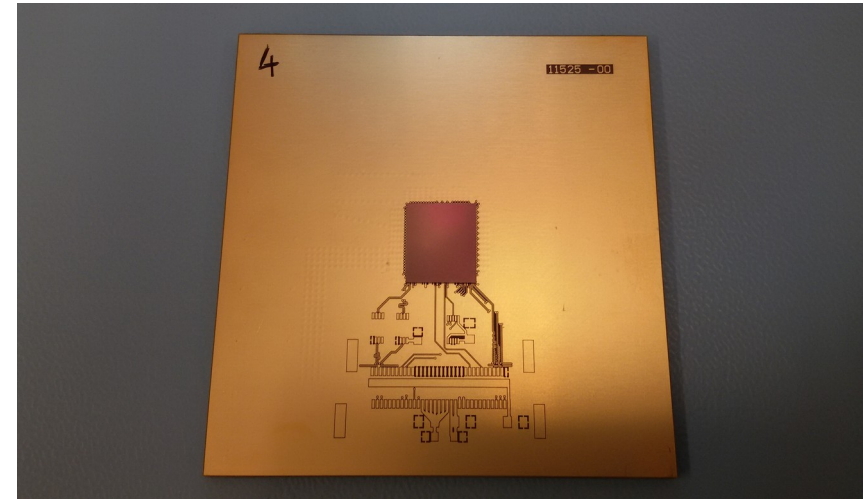
Concept

- Prototype board:
- PCB of 9 x 9 cm²
- 3 pad sizes and different connection lengths to be tested, smallest pads with shortest connections directly on the chip → influence of capacitance
- 500 channels connected in total
- To be used with 10 x 10 cm² GEMs in a small TPC
- ENEPIG coating for bonding



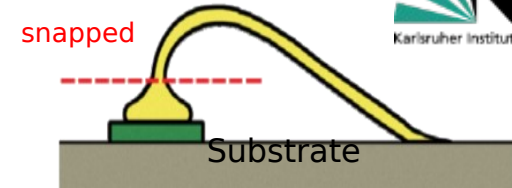
1st generation

- First 3 prototype boards were ordered for Nov 2016,
- 1st production: Jan 2017, no trough vias
- 2nd production: Mar 2017, bad metalisation
- 3rd production: May 2017, successful, only 2 boards
- First one bonded twice, second time successfully
- Second bonded with pillars was mechanically unstable
- Got 1 readout, then system broke

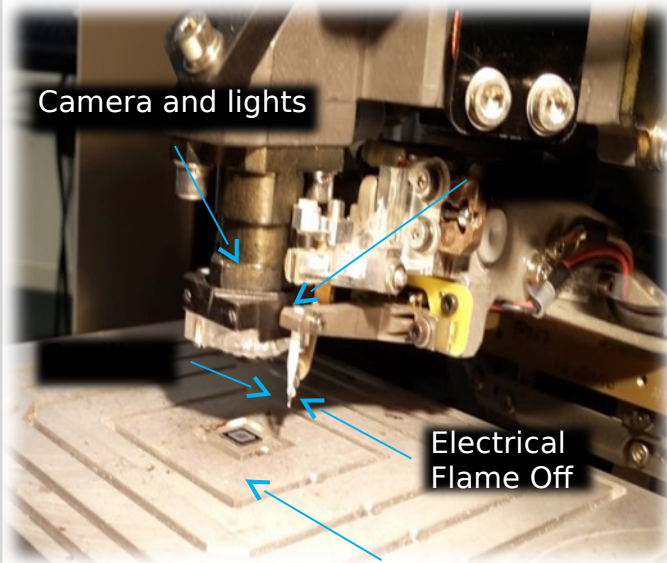


Stud Ball Bumping (SBB) process

Gold stud bumping is an evolution of the ~ 60 years-old wire bonding process. **Gold stud ball**: the wire is snapped off after the ball is initially connected to the substrate



Gold Ball-wedge wire-bonding



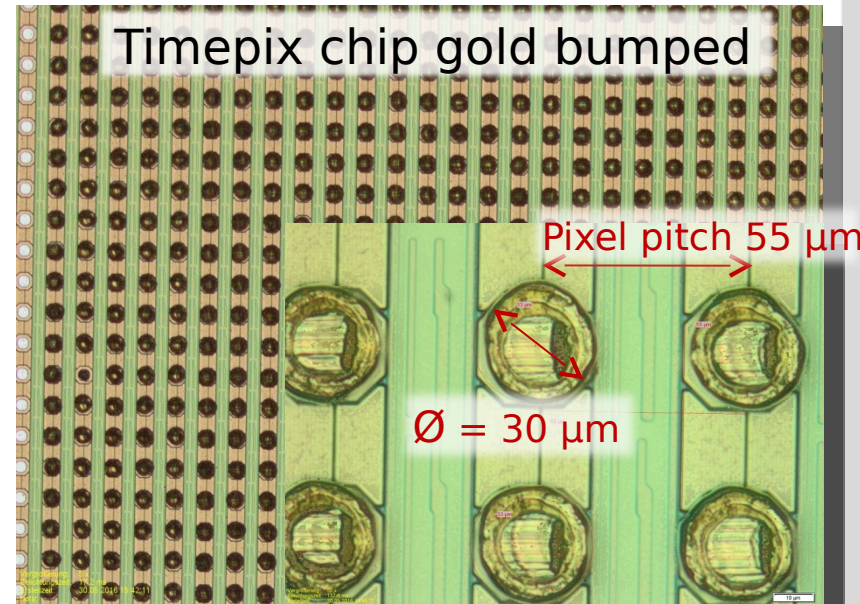
Achieved Bump & pitch size

Au wire diameter (μm)	Bump diameter (μm)	Minimum pitch (μm)
25	60	100
15	30	50
12.5	23	35

- ✓ **Low-cost process:** direct deposition on Al pad (No UBM, lithography process)
- ✓ **Fast deposition:** 20 bumps/s
- ✓ **Short setup time:** ideal for single die bump-bonding (i.e. prototype and R&D)

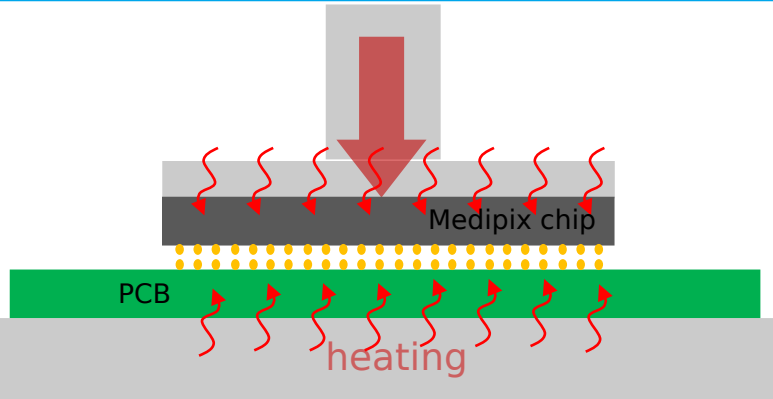


PCB gold bumped

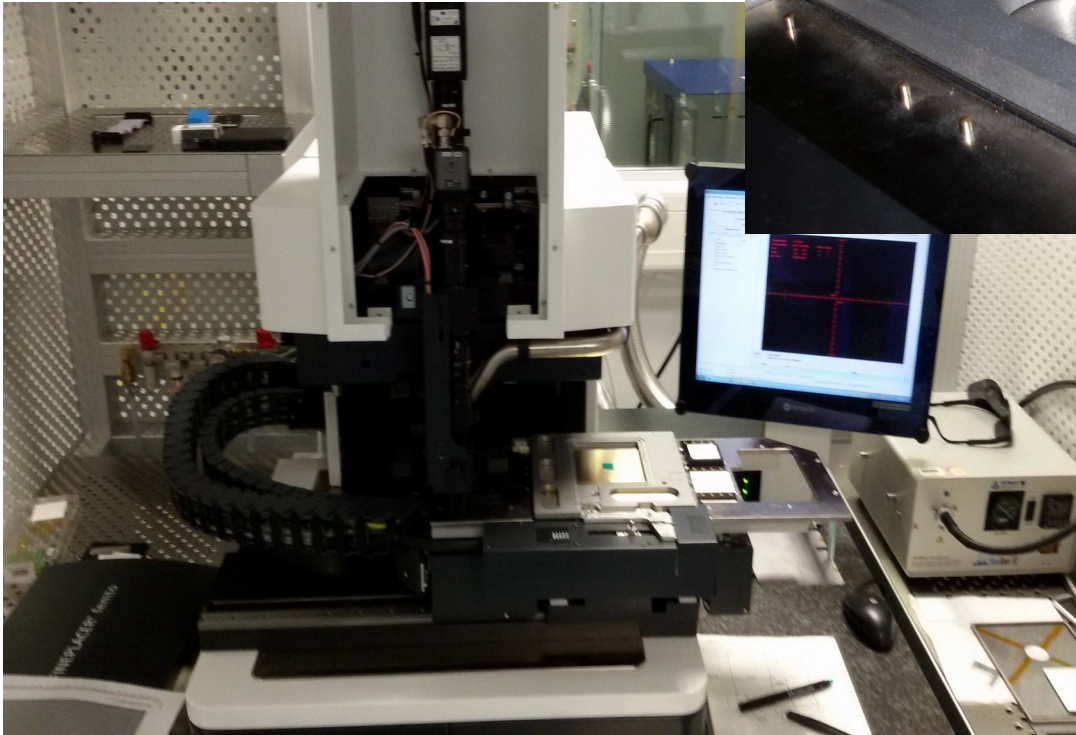
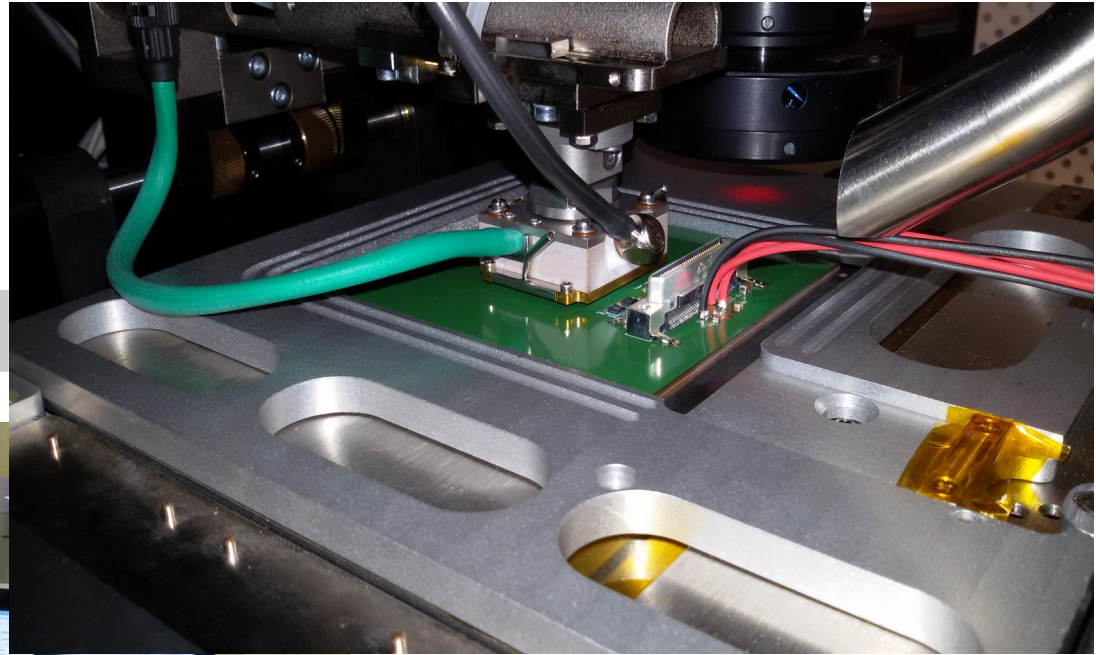


Timepix chip gold bumped

Flip-Chip Process - Bonding Maschine

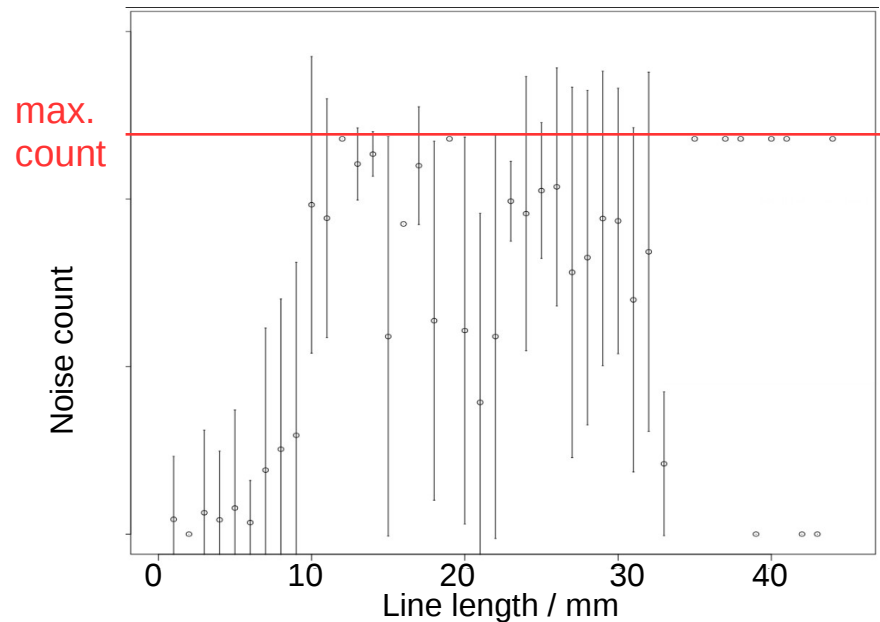
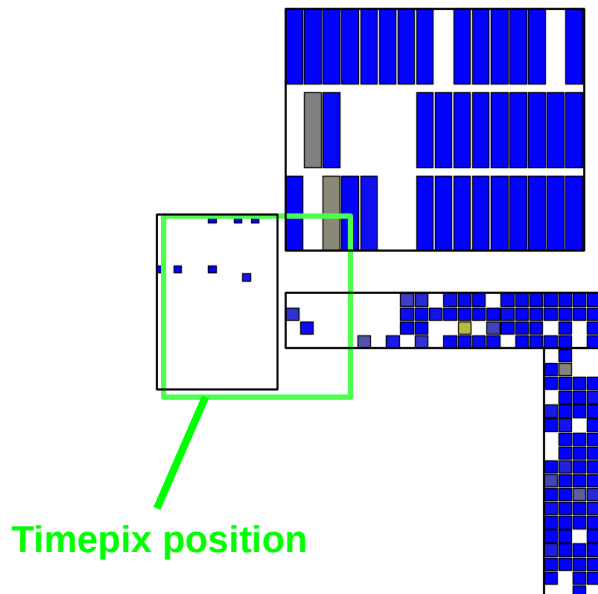


Thermo-compression Bonding process



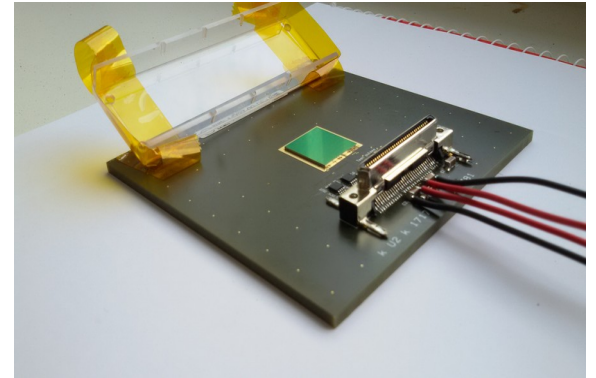
1st generation: Result

- Got 1 reasonably good data set (of noise) before system broke again
- Correlation between pad distance from Timepix and noise consistent with expectation
- Used threshold: 380 counts, typical: 300-400 counts, 1 count = 25 e-



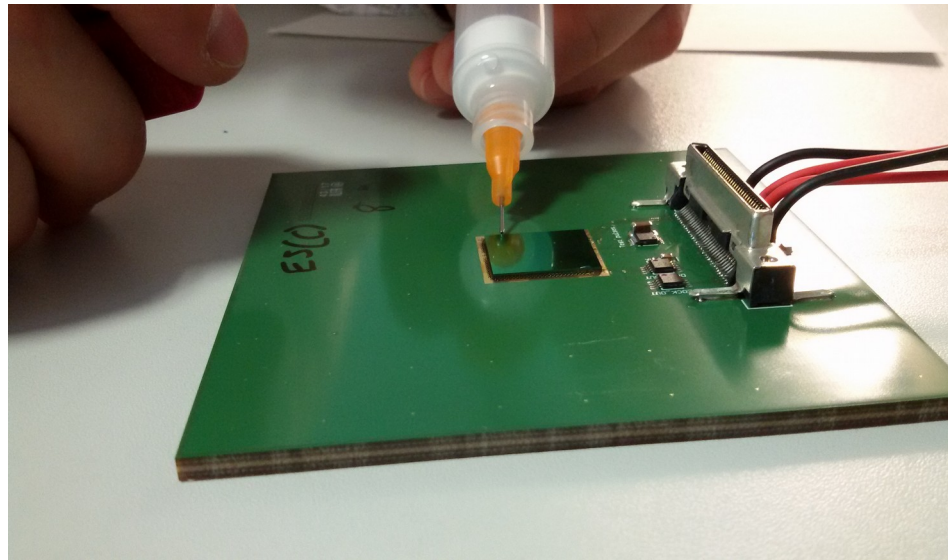
- Large errors, but some confidence reg. noise assumptions

- Biggest issue: coefficient of thermal expansion (CTE)
- This time:
 - PCB with lower CTE and lower bonding temperature
 - More boards
 - Immediate readout
 - Spent several days with group of people on bonding process
 - Michele Caselle, Markus Gruber, Patrick Pfistner and Sumera Kousar
 - 1. Apply gold studs from 25 μm wire to PCB
 - rather feasible, but O(10) by-hand corrections to be done
 - 2. Apply gold studs from 15 μm wire to Timepix
 - difficult to find correct parameters, optimise for bonding strength



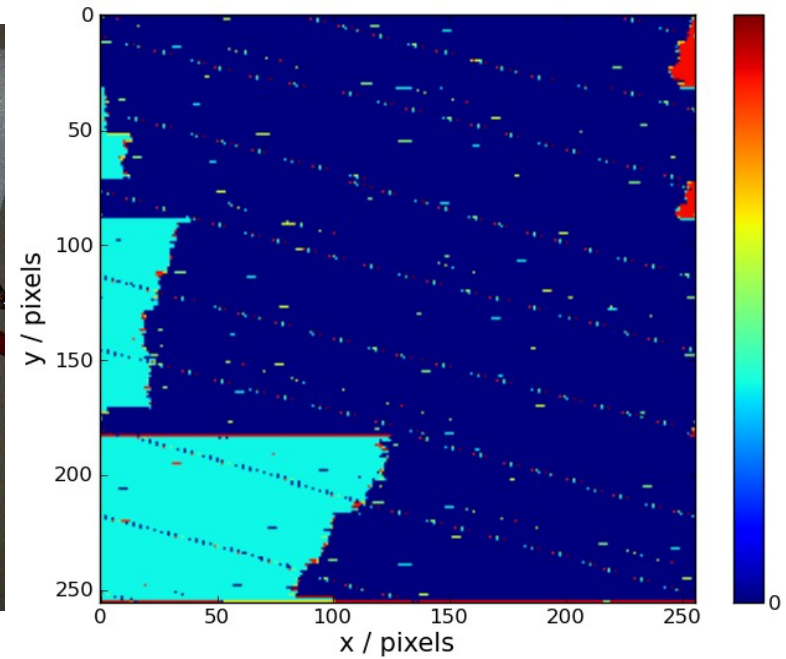
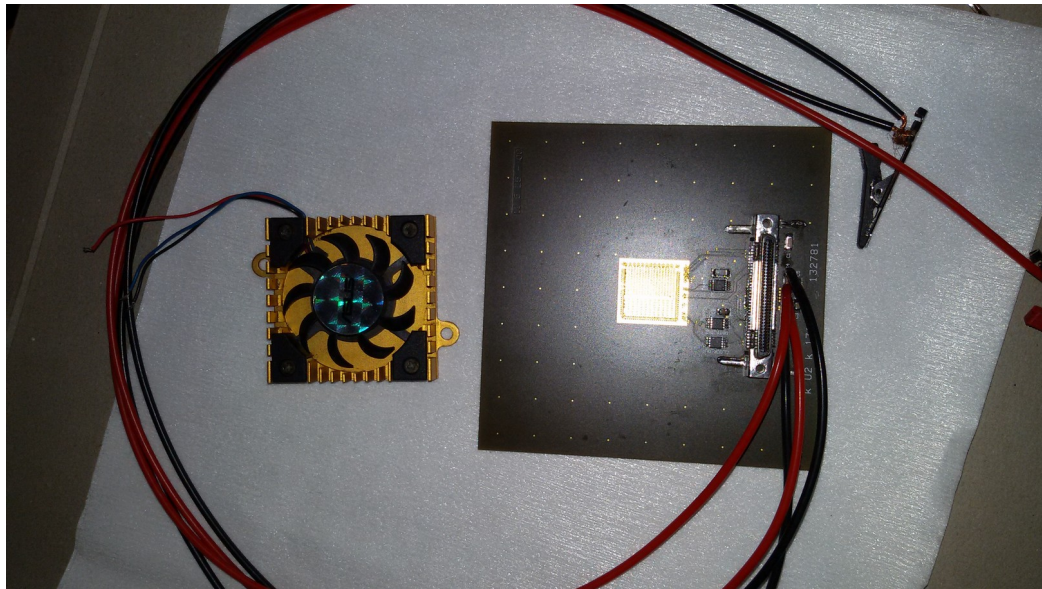
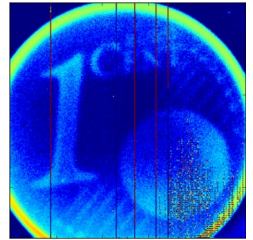
Bonding Result

- 7 boards bonded, 6 worked for at least some time, 3 worked in the end
- Data taken: 'threshold campaigns'
 - for different thresholds, runs with 100-200 frames
- Clear signs of temperature issue breaking connections
- Underfill applied to 3 boards for mechanical stability, taken to DESY



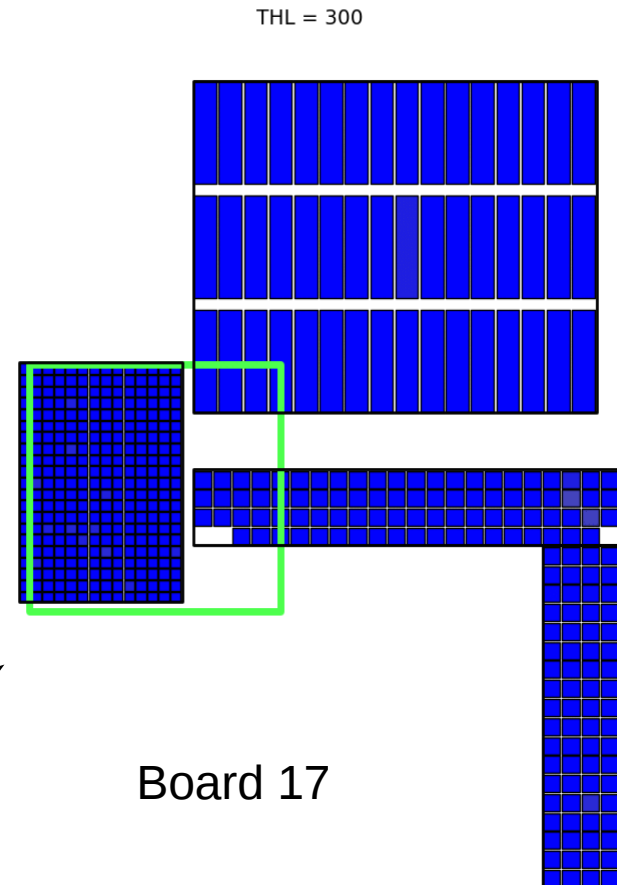
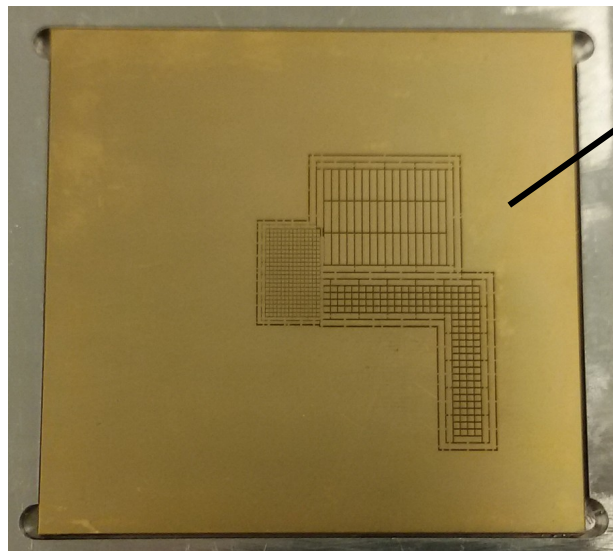
Back at DESY

- Applied active cooling blocks + fans to the chips
- One more 'threshold campaign' taken at DESY
- After that, all boards showed similar issues of probable bit shifts



First look into the data

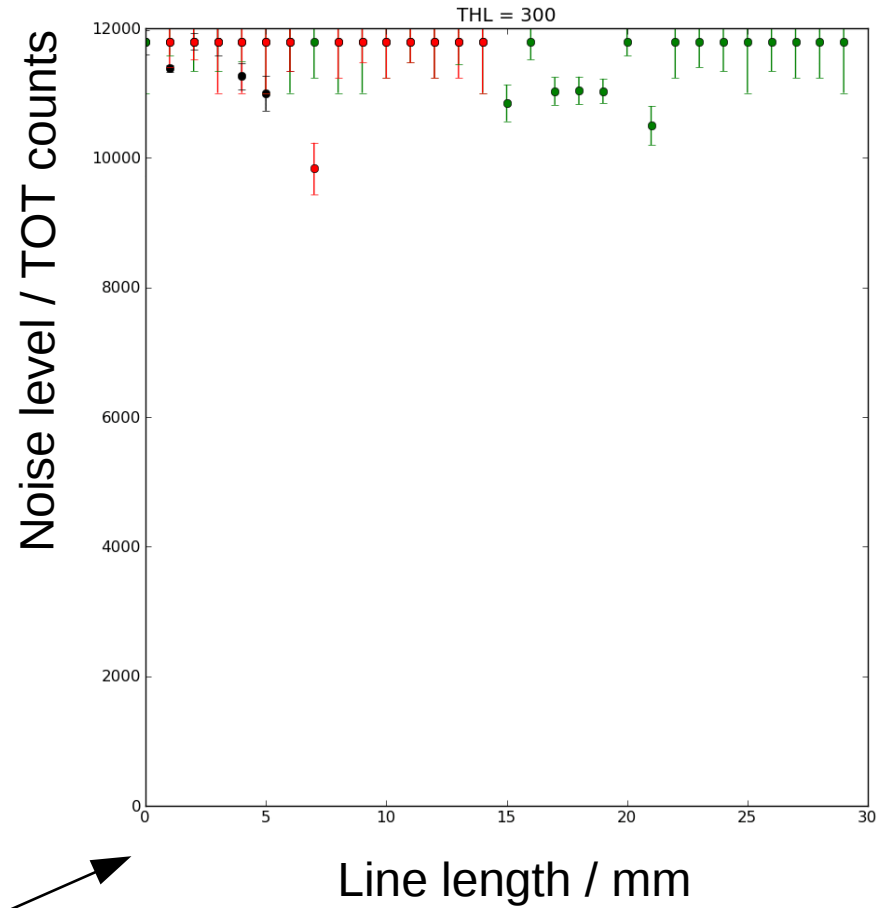
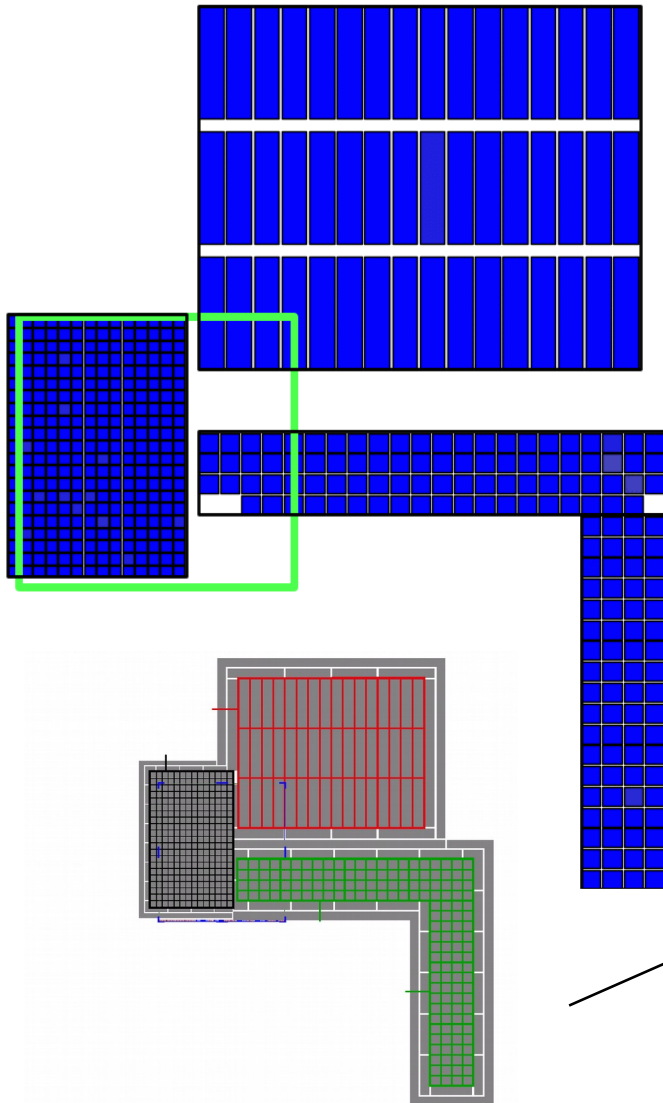
- Active pads in noise at different threshold levels
- Green: Timepix position
- Noise should depend on pad size and line length
- Done for 3 different board, not at the same thresholds



Noise vs. Line Length

Board 17

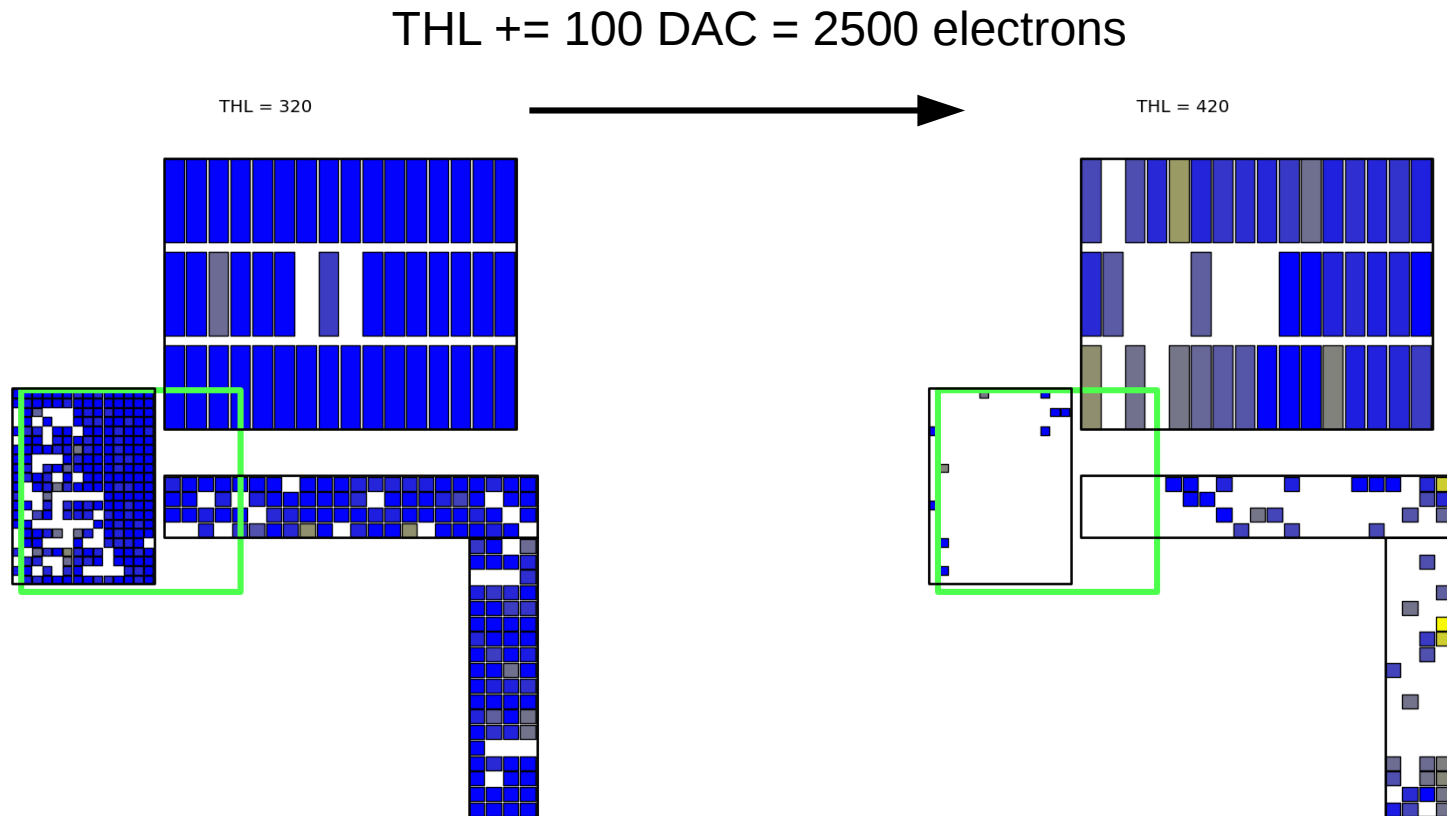
THL = 300



color
code

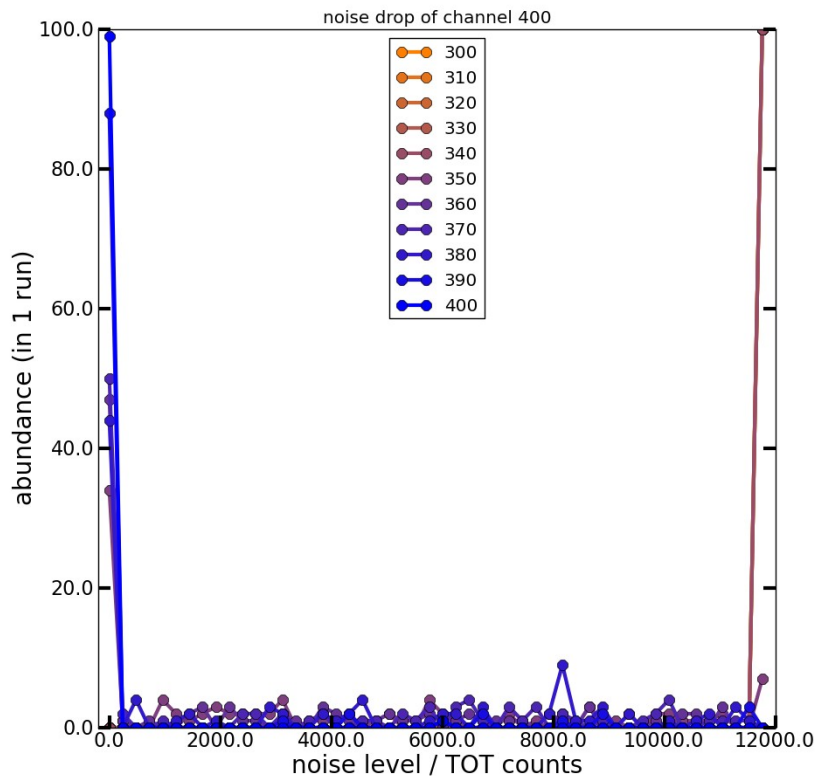


Observed noise drop



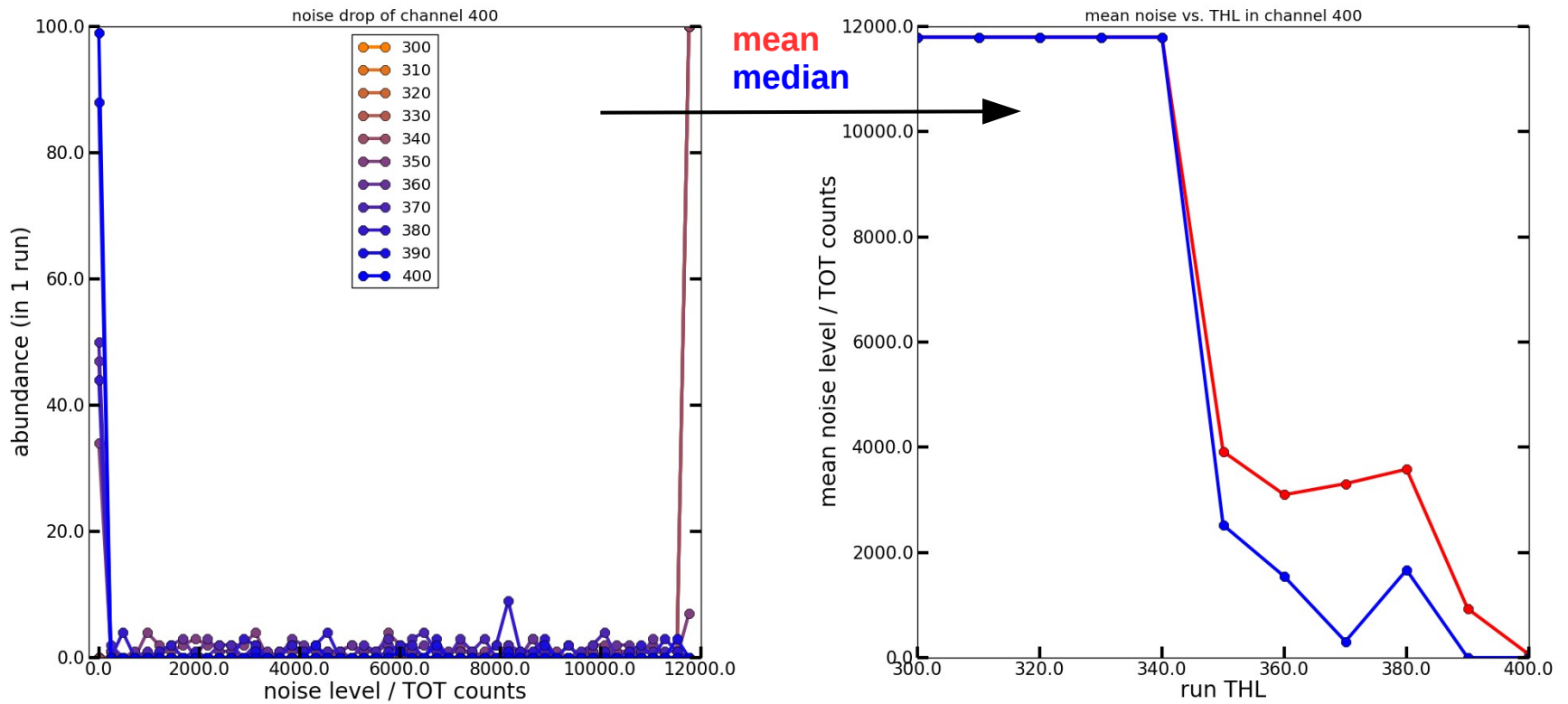
- For one channel: Take 100 frames and plot abundance of noise level, repeat for different thresholds

Take mean or median of the noise

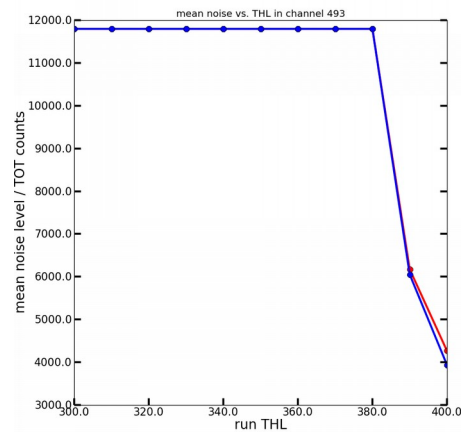
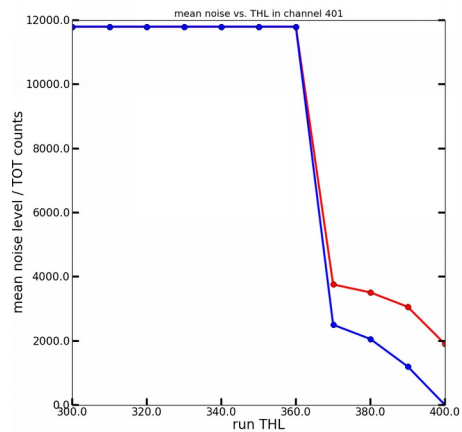
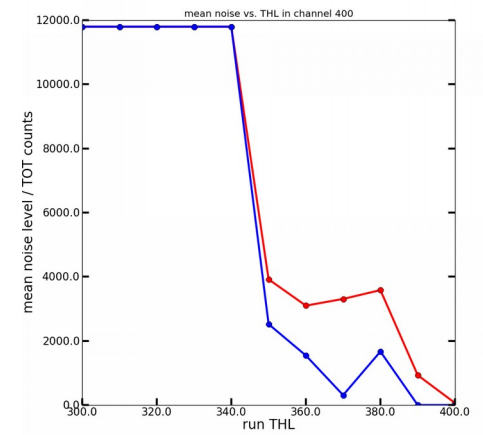
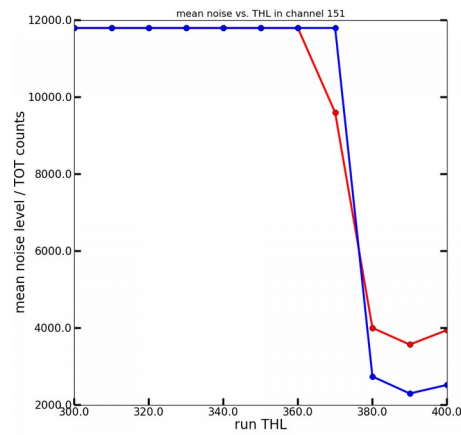
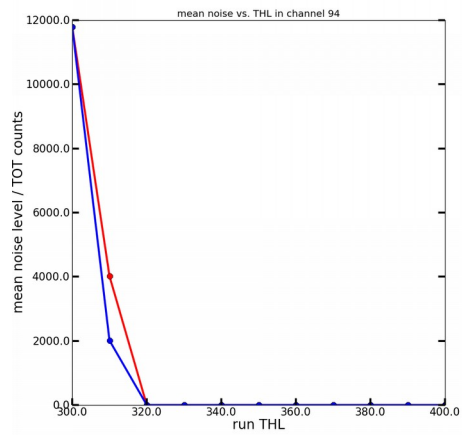


- Most times, the channel is completely silent (0) or completely noisy (11810).
- How does the transition look?
- Check mean and median abundance!

Take mean or median of the noise



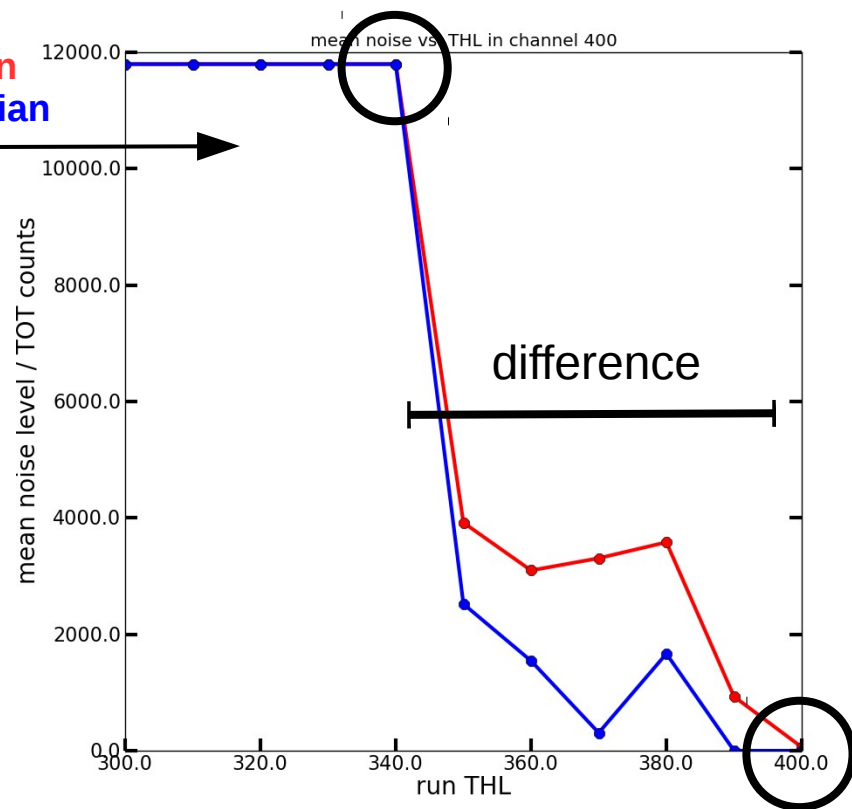
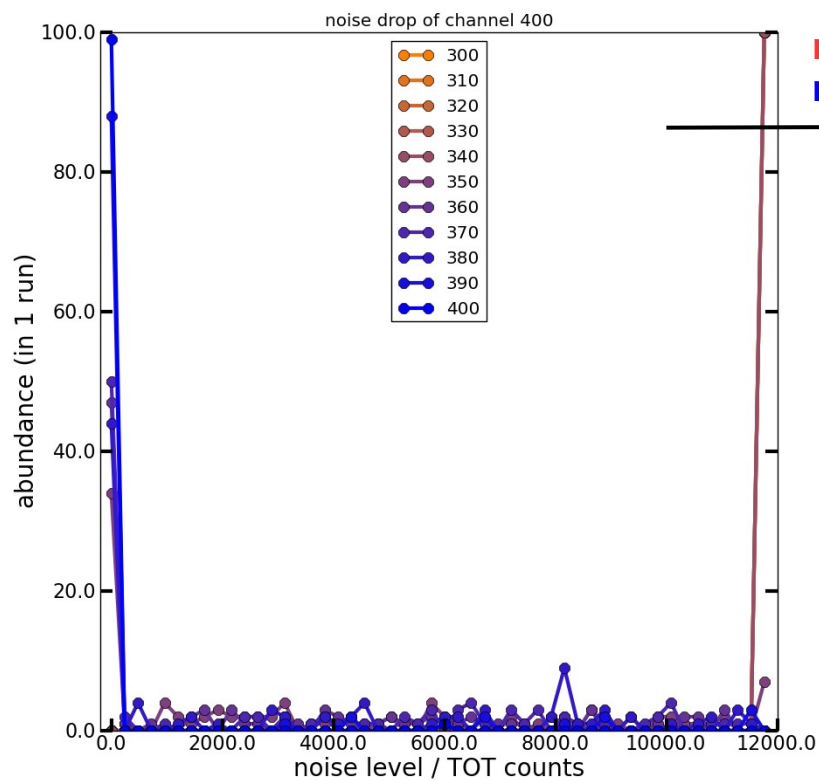
5 example channels



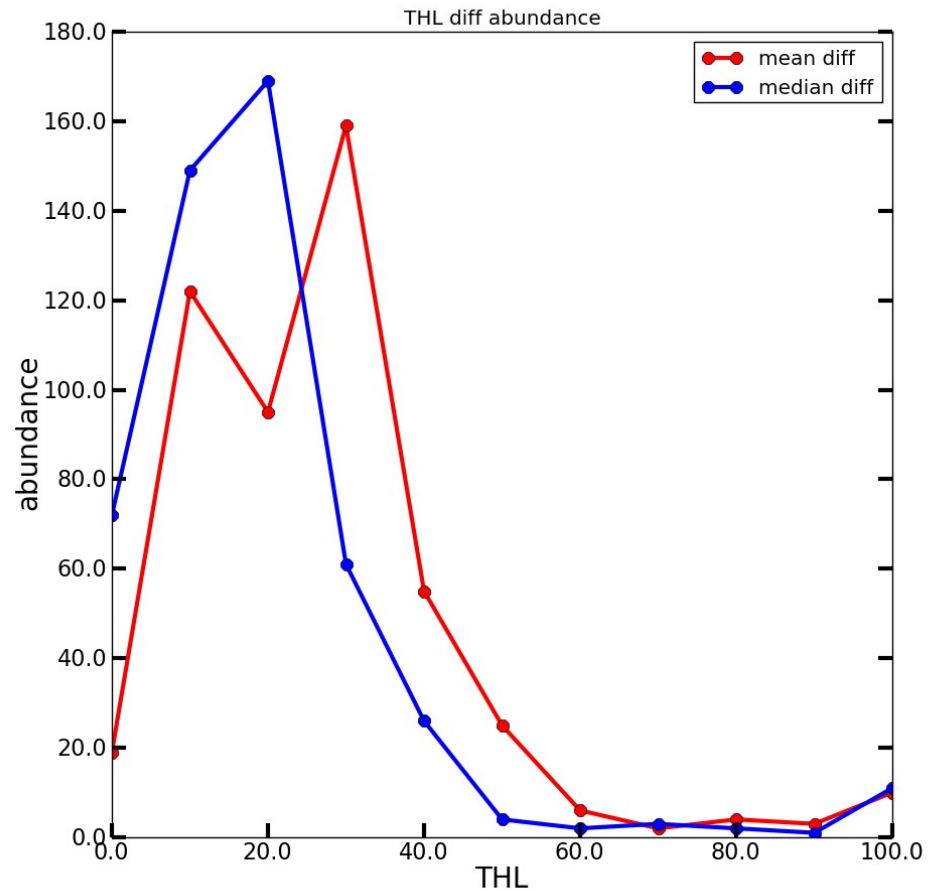
mean
median



Identify edges & difference



THL difference

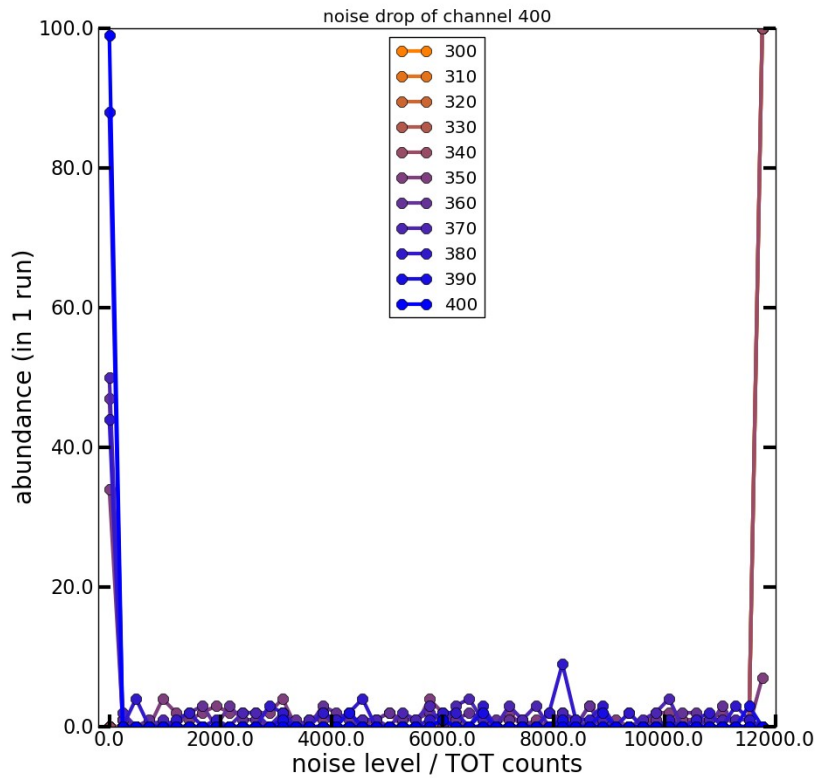


THL edge difference
is mostly below 50 DAC
→ $\sigma < 25$ DAC
= 625 electrons

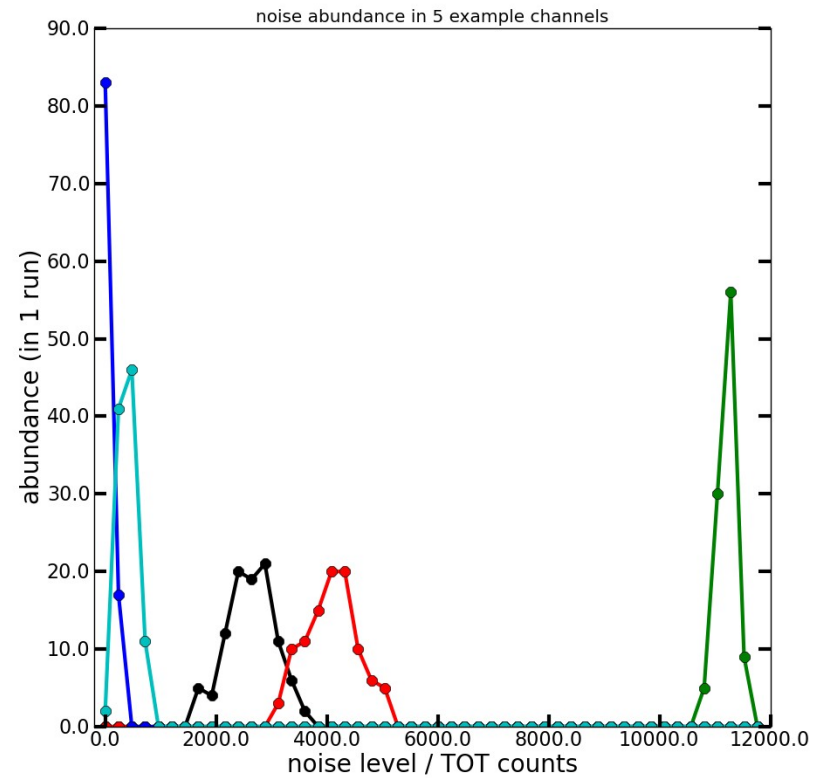


Comparison with bare Timepix

ROPPERI

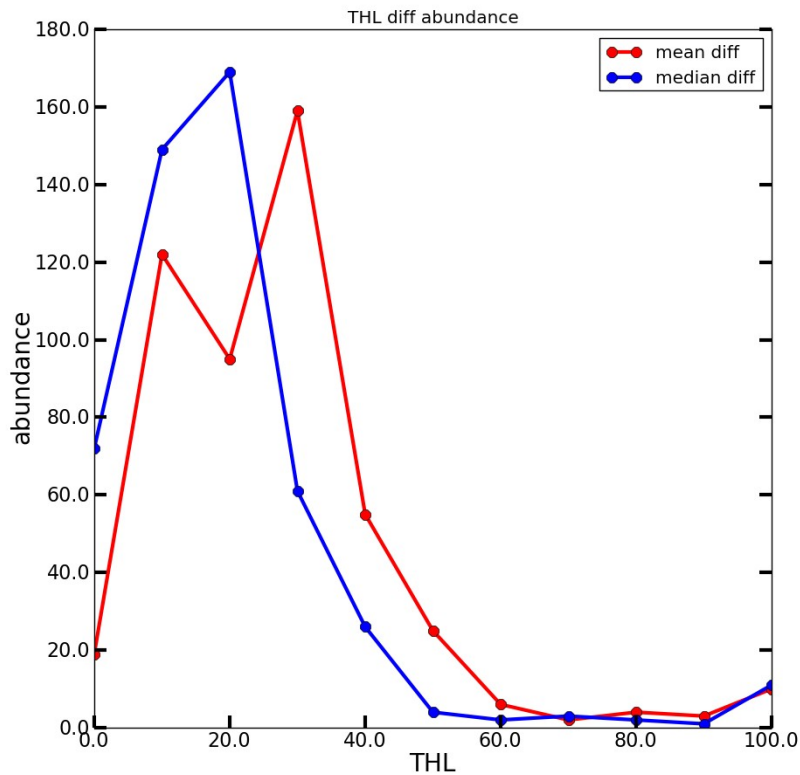


bare TP

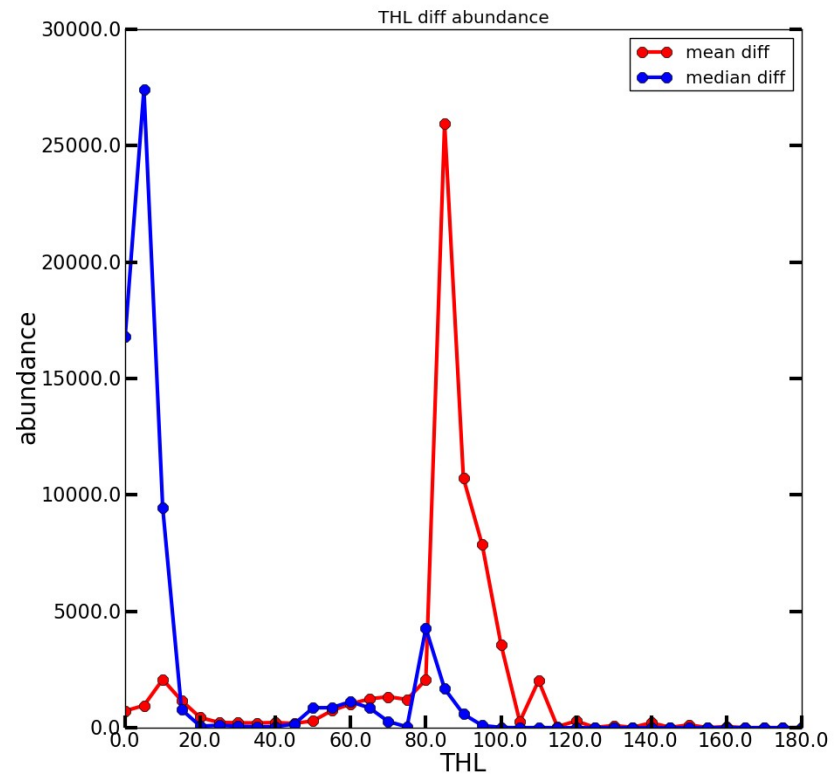


Comparison with bare Timepix

ROPPERI



bare TP



bTP: channels are unlikely to go into total noise or total silence, so by requiring the mean to be min/max the THL-difference gets very large. Taking the median compensates for this.



Comparison with bare Timepix

- ROPPERI board has about 3 times the noise as a bare Timepix with a known ENC of 90 electrons $\rightarrow \sim 300$ electrons for ROPPERI.
- So far, in simulation an automatic threshold of 560 electrons is applied.
- A by-eye comparison of simulation with no noise and with 500 electrons noise gives very similar results, plots are work in progress.
- A GEM-gain of 10k would allow the identification of a single electron with 3×3 $300 \mu\text{m}$ pads each receiving 3 ENC.
- Depending on the algorithm, combining 9 pads into one measurement, this increases the S/N by $\sqrt{9}=3$ to be 9.

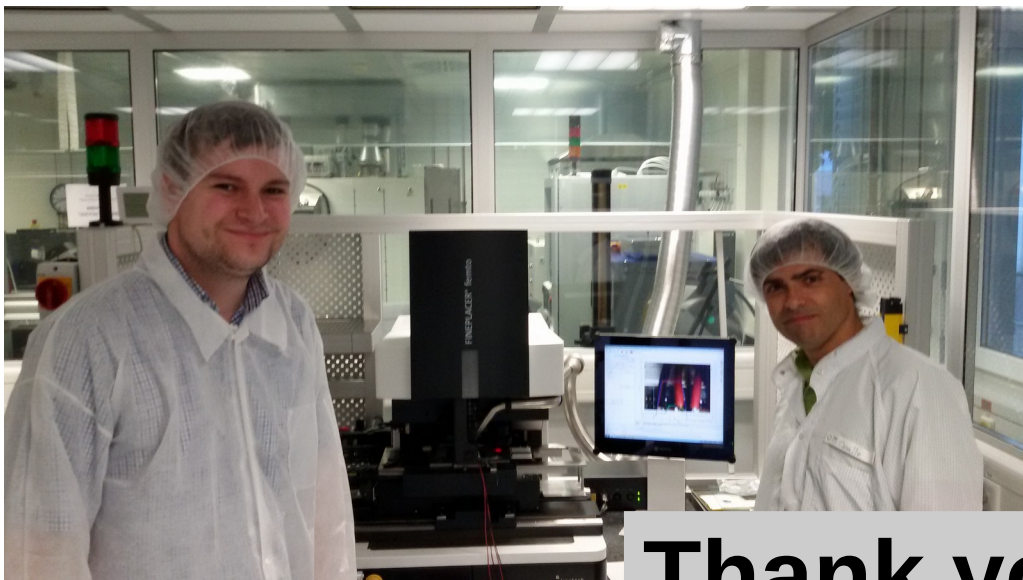


Conclusion

- An estimate for a equivalent-noise-charge for the ROPPERI system of about 300 electrons, as well as for a signal-to-noise level including MPGDs was calculated, the result is reasonable in combination with achievable GEM gains.
- The system built was still not stable, despite being optimised within the given base material category. The difference in CTE still destroyed the connections and made long-term measurements impossible.
- A new base material, e. g. ceramic, could be used. This would typically have a CTE much closer to silicon, as well as the potential of significantly smaller feature sizes.



The End



Thank you!

